

Title of Change:	Datasheet update for Vgs condition of maximum ratings and IGSS test condition
Effective date:	21 Jul 2026
Contact information:	Contact your local onsemi Sales Office
Type of notification:	This Product Bulletin is for notification purposes only. onsemi will proceed with implementation of this change upon publication of this Product Bulletin.
Change Category:	Datasheet update
Change Sub-Category(s):	Datasheet/Product Doc change

Sites Affected:

onsemi Sites	External Foundry/Subcon Sites
None	None

Description and Purpose:

onsemi wishes to inform customers of its plan to update datasheet parameters for SiC 650V MOSFET discrete products. The change involves revision of Gate-to-Source Voltage maximum ratings and Gate-to-Source Leakage current test conditions based on extended reliability validation results, including High Temperature Gate Bias (HTGB) and Dynamic Gate Stress (DGS) testing. These updates are intended to reflect improved product performance and reliability capability.

1. MAXIMUM RATINGS

Parameter	Symbol	Value		Unit
		Current	Updated	
Gate-to-Source Voltage	V_{gs}	-8/22	-10/22.6	V
Gate-to-Source Transient Voltage	V_{gs}	tp<0.5us, Duty Cycle≤1%	-11/25	V

2. ELECTRICAL CHARACTERISTICS

	Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Current Datasheet	Gate-to-Source Leakage Current	I_{GSS}	VGS=-8/22V, VDS=0V	-	-	±1.0	μA
Updated Datasheet	Gate-to-Source Leakage Current	I_{GSS}	VGS=-10/22.6V, VDS=0V	-1	-	1	μA

The change will not impact form, fit, or function of products.

List of Affected Standard Parts:

Note: Only the standard (off the shelf) part numbers are listed in the parts list. Any custom parts affected by this PCN are shown in the customer specific PCN addendum in the PCN email notification, or on the [PCN Customized Portal](#).

NTBG023N065M3S	NTBG032N065M3S	NTBL023N065M3S
NTH4L032N065M3S	NTH4L023N065M3S	NTBL032N065M3S